# MSKSEMI 美森科













ESD

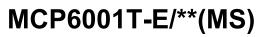
TVS

TSS

MOV

GDT

PLED



**Product specification** 







## **GENERAL DESCRIPTION**

The MCP6001T-E/\*\*(MS)is a CMOS operational amplifier that uses the proprietary auto-calibration technique to simultaneously provide very low offset voltage,near-zero drift over time and temperature. This miniature, high-precision, low quiescent current amplifiers offer high-impedance inputs that have a common-mode range 200mV beyond the rails, and rai-to-rail output that swings within 50mV of the rails, single or dual supplies as low as  $2.1V(\pm 1.35V)$  and up to  $5.5V(\pm 2.75V)$ can be used. This device is optimized for low voltage, single supply operation.

The MCP6001T-E/\*\*(MS)offers excellent CMRR without the crossover associated with traditional complementary input stages. This design results in superior performance for driving analog-to-digital converters (ADC) without degradation of differential linearity.

Applications

Electronic Scales

Medical instrumentation

Handheld Test Equipment

Measurement

Transducers

Temperature

The MCP6001T-E/\*\*(MS)is available in the 5-pin SOT-23-5 and SC70-5 packages,and specified for operation from -55℃ to 125℃.

#### **FEATURES**

- VDD range:2.1V to 5.5V
- Low Ofset Voltage:0.5mV (Typical)
- Low Drift:0.65µV/C(Typical)
- Low Noise
- Quiescent Current:28µA
- Rail to Rail Input/Output
- MicroSize Packages:SC70-5 and SOT23-5

#### **Reference News**

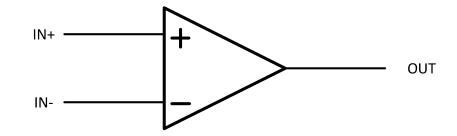
	PACKAGE OUTLINE		PIN CONFIGURATION	Marking		
			OUT 1 VSS 2 IN+ 3 4 IN-	CD**	CD**	
Ĩ	SOT-23-5	SC70-5	SOT-23-5/SC70-5	SOT-23-5	SC70-5	

#### **PIN DESCRIPTION**

Pin Name	Pin Numbel	Description	
1 IN+	1	Noninverting inpu	
GND	2	Negative(lowest)power supply	
1 IN-	3	Inverting inpu	
OUT	4	Output	
Vcc+	5	Positive (highest)power supply	



## SIMPLIFIED SCHEMATIC



**Figure 1.Simpliied Schematic** 

# ABSOLUTE MAXIMUM RATINGS

Thermal Resistance 0 Jc	130°C/W
Supply Voltage	2.1to 5.5V
Signal Input Terminals Voltage0.	1 to (V+)+0.1V
Operating Junction Temperature	<b>150</b> ℃
Operating Temperature Range	25°C to 85°C
Storage Temperature	<b>-65°℃ to 150</b> ℃



# **ELECTRICAL CHARACTERISTICS**

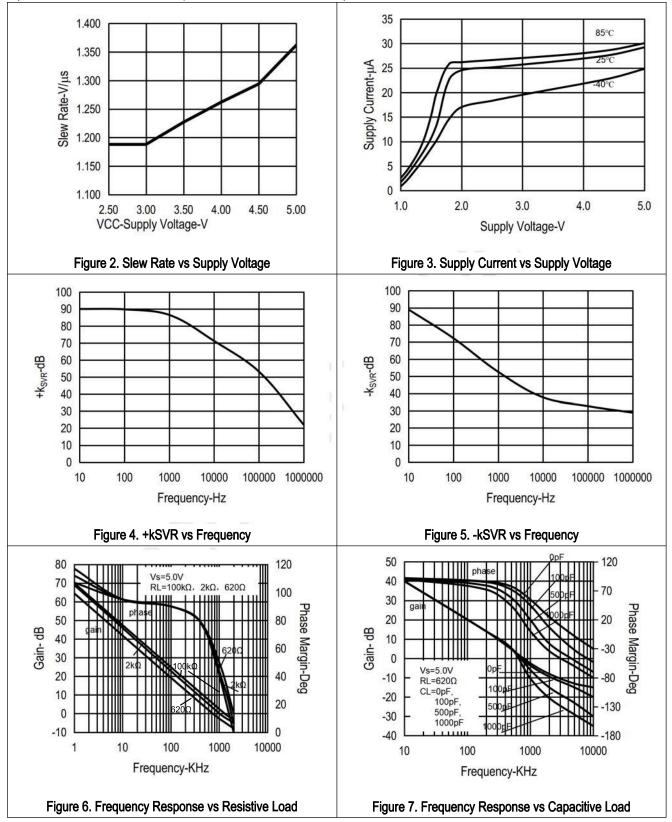
(At TA=25° C, RL=10k connected to Vs/2, and Vour=Vs/2, unless otherwise noted.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Input Offset Voltage	Vs=±2.5V	-3	0.5	3	mV
nput Offset Voltage Drift	TA=-55°℃ to 125°℃		0.65		μV/°C
Power Supply Rejection Ratio	Vs =2.1V to 5.5V TA=-55℃ to 125℃	80	90		dB
Input Bias Curren	TA=25℃		2.0		рА
Input Offset Current			1.0		pА
Common-mode Voltage Range		(V-)-0.1		(V+)+0.1	V
Common-mode Rejection Ratio	V-)-0.1 <vcm<(v+)+0.1 TA=-55℃ to 125℃</vcm<(v+)+0.1 	80	95		dB
Open Loop Voltage Gain	(V-)+100mV <vo<(v+)-10 OmV, RL=10k TA=-55° ℃ to 125℃</vo<(v+)-10 	80	100		dB
Gain-bandwidth product	CL=120pF		1.5		MHz
Slew Rate	G=+1		1.2		V/µs
Specified Voltage Range		1.8		5.5	V
Quiescent Current			28	40	μA
Operating Temperature Range		-25		85	°C
Storage Temperature Range		-65		150	°C



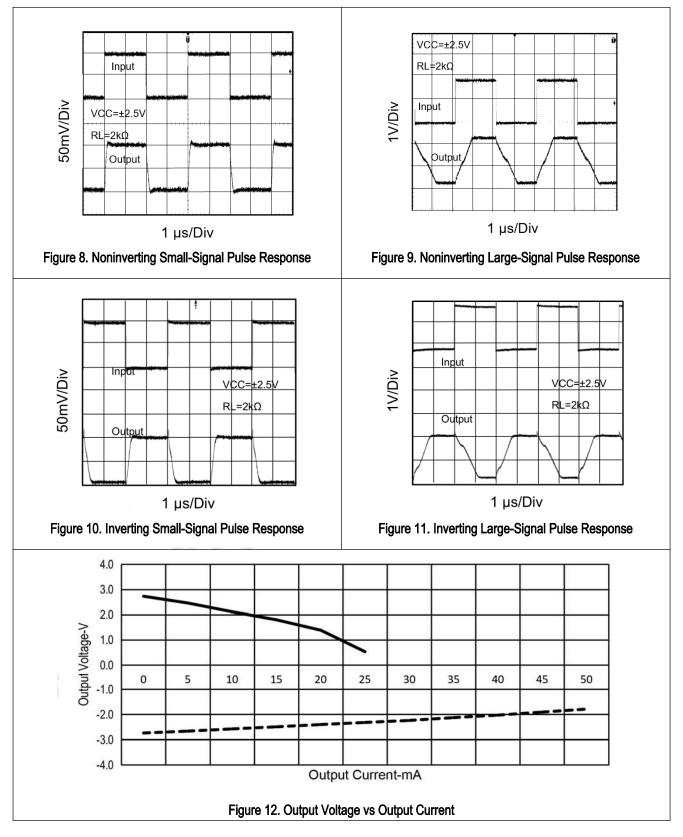
# **TYPICAL PERFORMANCE CHARACTERISTICS**

(At T<sub>A</sub> = 25°C,V<sub>S</sub>=5V, C<sub>L</sub>=20pF, unless otherwise noted.)





# **TYPICAL PERFORMANCE CHARACTERISTICS**





# FUNCTIONAL DESCRIPTION

#### **Operating Voltage**

The MCP6001T-E/\*\*(MS)devices are fully specified and ensured for operation from 2.1V to 5.5 V.In addition,many specifications apply from -55°C to 125°C. Parameters that vary significantly with operating voltages or temperature are shown in the Typical Characteristics graphs.

#### **Unity-Gain Bandwidth**

The unity-gain bandwidth is the frequency up to which an amplifier with a unity gain may be operated without greatly distorting the signal.The MCP6001T-E/\*\*(MS)device has a 1.5-MHz unity-gain bandwidth.

#### **APPLICATIONS INFORMATION**

The MCP6001T-E/\*\*(MS)is a unity-gain stable,precision operational amplifier with very low offset voltage drift; these devices are also free from output phase reversal.Applications with noisy or high-impedance power supplies require decoupling capacitors close to the device power-supply pins.In most cases, 0.1µF capacitors are adequate.

#### **Typical Application**

Figure 13 shows a simple circuit to convert a single-ended input into differential output.The MCP6001T-E/\*\*(MS) could be used to build this circuit.The circuit is composed of two amplifiers.One amplifier acts as a buffer and creates a voltage,VouT+.The second amplifier inverts the input and adds a reference voltage to generate Vour-.Both Vour+ and Vour-range from 0.5 to 2 V.The diference, VDIFF, is the difference between Vour+and VouT-.

#### **Slew Rate**

The slew rate is the rate at which an operational amplifier can change its output when there is a change on the input. The MCP6001T-E/\*\*(MS)devices have a1 .2-V/µ s slew rate. The MCP6001T-E/\*\*(MS)is characterized toperform with this technique; the recommended resistor value is approximately 20 k.

#### **Device Functional Modes**

The MCP6001T-E/\*\*(MS)device has a single functional mode. The device is powered on as long as the power supply voltage is between 2.1V(±1.35V)and 5.5V(±2.75V)

#### **Detailed Design Procedure**

Linearity over the input range is key for good dc accuracy. The common mode input range and the output swing limitations determine the linearity. In general, an amplifier with rail-to-rail input and output swing is required. Bandwidth is a key concern for this design. Because MCP6001T-E/\*\*(MS)has a bandwidth of 1MHz, this circuit will only be able to process signals with frequencies of less than 1 MHz.

Because the transfer function of Vour-is heavily reliant on resistors(R1,R2,R3,and R4),use resistors with low tolerances to maximize performance and minimize error.This design used resistors with resistance values of 36 k with tolerances measured to be within 2%.If the noise of the system is a key parameter,the user can select smaller resistance values (6 k or lower)to keep the overall system noise low.This ensures that the noise from the resistors is lower than the amplifier noise.



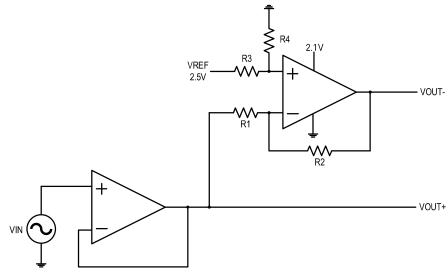
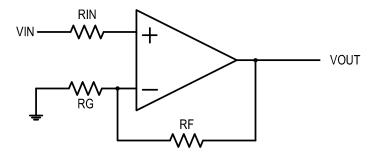


Figure 13. Schematic for Single-Ended Input to Differential Output Conversion

# LAYOUT

Use good PCB layout practices for best operational performance of the device, including:

- Keep the length of input traces as short as possible.
- Run the input traces as far away from the supply lines as possible to reduce parasitic coupling.
- Place components close to device and to each other to reduce parasitic capacitance and parasitic errors.
- Use low-ESR, ceramic bypass capacitors to reduce the coupled noise by providing low impedance power sources local to the analog circuitry.
- Grounding for analog and digital portions of circuitry separately to suppresse the noise.





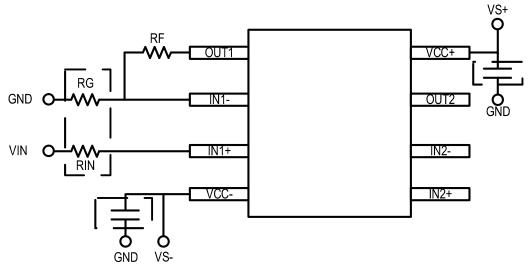
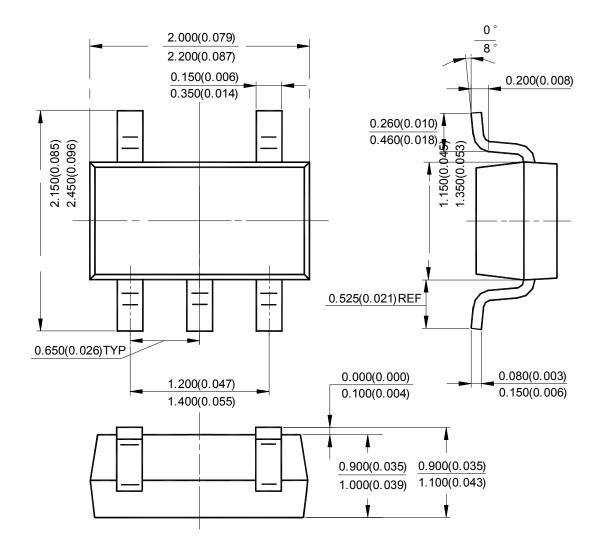


Figure 14. Operational Amplifier Schematic and Board Layout for Noninverting Configuration



#### Package Outline Dimensions (All dimensions in mm(inch).)

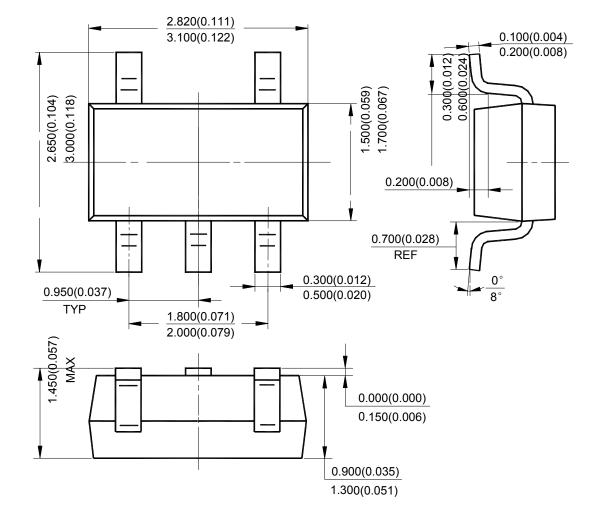


SC-70-5





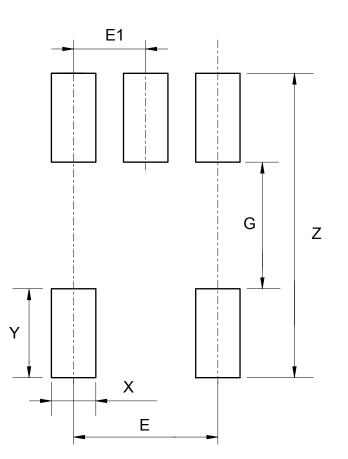
## Package Outline Dimensions (Cont. All dimensions in mm(inch).)



SOT-23-5



# Suggested Pad Layout

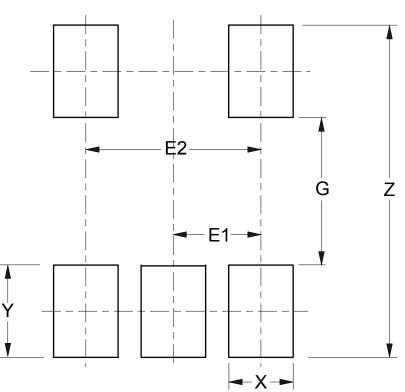


Dimonsions	Ζ	G	Х	Y	Е	E1
Dimensions	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)
Value	2.740/0.108	1.140/0.045	0.400/0.016	0.800/0.031	1.300/0.051	0.650/0.026





Suggested Pad Layout (Cont.)



Dimensions	Ζ	G	Х	Y	E1	E2
Difficitsions	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)
Value	3.600/0.142	1.600/0.063	0.700/0.028	1.000/0.039	0.950/0.037	1.900/0.075

SOT-23-5



# **REEL SPECIFICATION**

P/N	PKG	QTY
MCP6001T-E/OT(MS)	SOT-23-5	3000
MCP6001T-E/LT(MS)	SC70-5	3000



## **Attention**

Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.

Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuits for safedesign, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or

mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements intellectual property rights or other rights of third parties.

Any and all information described or contained herein are subject to change without notice due to

product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.

单击下面可查看定价,库存,交付和生命周期等信息

>>MSKSEMI (美森科)